M any Body E ects on the Transport Properties of Single-M olecule Devices

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The conductance through a molecular device including electron-electron and electron-phonon interactions is calculated using the Numerical Renorm alization G roup method. At low temperatures and weak electron-phonon coupling the properties of the conductance can be explained in terms of the standard K ondo model with renorm alized parameters. At large electron-phonon coupling a charge analog of the K ondo elect takes place that can be mapped into an anisotropic K ondo model. In this regime the molecule is strongly polarized by a gate voltage which leads to rectile cation in the current-voltage characteristics of the molecular junction.

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E lectronic conduction through nanoscale system s connected to external electrodes exhibits a num ber of special features that are of great im portance when one considers their potential as electronic devices.

The transport properties of such system s are strongly a ected by (e-e) and electron-phonon (e-ph) interactions. For example, C oulom b blockade e ects have been shown to dom inate the transport in quantum dots [1] and even in single m olecules weakly coupled to the electrodes [2, 3]. The K ondo e ect has been observed in quantum dots [4] and single m olecules having well de ned spin and charge states [2, 5, 6]. Furtherm ore the e ects of e-ph coupling have been observed in Inelastic E lectron Tunneling Spectra of sm all m olecules adsorbed on surfaces [7] and in m olecular-scale transistors m ade of C₆₀ m olecules [8]. Finally, e-ph coupling is also known to play an im – portant role in the transport through organic conjugated m olecules in which transport is m ediated via polaron or soliton propagation [9].

It is usually assumed that energy scales for e-e interaction are much larger than those for e-ph interaction. However, it has been recently shown that C oulom b charging energies of single molecules can be considerably reduced by screening due to the electrodes [3]. These energies can be of the order of a few 100 m eV (instead of a few eV for an isolated molecule) and therefore are of the same order of magnitude of the relaxation energies induced by e-ph coupling in the same systems. Interesting physics then arises when the energy scales of e-e and e-ph interactions merge. By studying such cases, insights on the origin of the features in the conductance can be brought and the in uence of the e-ph coupling on the K ondo e ect can be addressed.

A lthough there have been m any theoretical investigations of electron transport in the presence of either e-e or e-ph interactions, the case in which both interactions are present has only been studied recently [10, 11, 12] either in the high tem perature or weak e-ph coupling regimes.

In this Letter, we report results of non-pertubative calculations of the linear transport properties through a m olecular device including e-e and e-ph interactions. The calculations are performed using the Numerical Renorm alization G roup (NRG) technique for a broad range of characteristic param eters.

W e study a model of a molecule with a single relevant electronic level coupled linearly to a vibrational mode of frequency $!_0$ and to the left (L) and right (R) metallic electrodes. The Ham iltonian of the system is

$$H = H_{M} + H_{E} + H_{M} _{E};$$
 (1)

where the rst two terms describe the isolated molecule and electrodes, respectively, and the last term describes their coupling. We have

$$H_{M} = "_{d}n_{d} + U n_{d} n_{d\#}$$
 (nd 1) a + a^y (2)
+ !_Qa^ya;

$$H_{E} = \prod_{k; j = fL; Rg}^{X} (k) c_{k}^{y} c_{k} ;$$
(3)

$$H_{M E} = V_{k} d^{y} c_{k} + c_{k}^{y} d :$$
(4)

Here, $n_d = \int^y d$ is the charge of the molecule, "_d is the position of the electronic molecular level relative to the Ferm i level of the electrodes and U is the Coulomb repulsion between two electrons that occupy the same molecular level. a^y creates a phonon of frequency !₀ and is the e-ph coupling constant. We consider for simplicity the case of identical electrodes and contacts. In the wide-band lim it the conductance G of the molecular junction at zero bias is [13, 14]

$$G = \frac{dI}{dV}_{V=0} = \frac{2e^2}{h} \qquad \begin{bmatrix} Z & 1 \\ 1 & d! \end{bmatrix} = \frac{e^2}{e^2} \qquad \begin{bmatrix} Q & f(!) \\ 0 & 0 \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \qquad \begin{bmatrix} e & f(!) \\ 0 & 0 \end{bmatrix} \end{bmatrix} \end{bmatrix}$$

where $_{d}(!) = {}^{1} \text{Im} G_{dd}(!)$, $G_{dd}(!)$ is the exact electronic G reen function of the molecule in the presence of the leads, f(!) the Ferm i distribution and = $2 {}_{0}hV_{k}^{2}i_{FS}$. Here, $_{0}$ is the electrodes' electronic density of states at the Ferm i level and the brackets denote an average over the Ferm i surface. Ham iltonian (1) is electron-hole symmetric for all values of at $"_{d} = "_{d}^{2} = U = 2$ where $h_{d}i = 1$. This point we will referred to as the symmetric point in the following.

At zero tem perature Eq. (5) reads

$$G = G_0 \qquad d(0) = G_0 \sin^2(m_d i=2);$$
 (6)

where $G_0 = 2e^2 = h$ is the quantum of conductance and the second equality follows from Luttinger's theorem [15]. At T = 0 the conductance G thus takes its maximum value G_0 at the symmetric point.

Before presenting the results of a full numerical solution of the problem we discuss two limiting cases that can be treated analytically providing us with a qualitative picture of the dependence of G upon T and $"_d$.

The H am iltonian H $_{\rm M}$ of the isolated molecule can be readily diagonalized. The eigenfunctions are direct products of electronic states (denoted by a subscript e) and oscillator states. The eigenstates and eigenvalues are

where $U' = \exp = !_0 a^y$ a and jn i is the m-th excited state of the harm onic oscillator. Two limiting cases can be considered.

W eak electron-phonon coupling, 2 2 =! $_{0}$ U. In this case the ground-state of the isolated molecule is the spindoublet j;0i. There is a large charge excitation gap $U_{e} = U = 2^{2}$ =! $_{0}$ at the symmetric point and the low-energy excitations of the full system are spin uctuations described by the usual K ondo H am iltonian [15]. Using standard second-order perturbation theory the coupling constant can be expressed in terms of a single matrix element: h;0 $H_{M} = 10$;m ih0;m $H_{M} = 1$;0i = h;0 $H_{M} = 10$;m ih0;m $H_{M} = 1$;0i / 1000^{+1} jn if. At "d = "d we nd the K ondo coupling constant [16]

where $\mathfrak{M} \mathfrak{M} \mathfrak{M}^+$ in $\mathfrak{i} \mathfrak{f} = e^{(-!_0)^2} (-!_0)^{2m} = \mathfrak{m} !$

Below the K ondo tem perature $T_K / exp \left[1 = (J_{K \ 0}) \right]$, G $(I_d^{(2)})$ G₀. Expanding Eq. (8) around = 0 we nd $J_K = J_K \ (0)$ 1 + 2 $\left[1 + U = (2!_0) \right]^{-1-2} = (U!_0)$. The e-ph coupling thus leads to an increase of the K ondo tem perature in this regime. For $T > T_K$, C oulom b blockade peaks separated by U_e are expected at gate voltages $I_d^{-2} = !_0$ and I_d^{-1} U + $^2 = !_0$.

Expanding Eq. (6) around the symmetric point we have G ($"_d$) G ($"_d^2$) G ($_c = 2$)² ($"_d = "_d^2$)², where c is the charge susceptibility, inversely proportional to the charge gap. The width of the T = 0 conductance peak, $"_d = c^1 = U_e$, decreases with increasing in the weak coupling regime.

Strong electron-phonon coupling, $2^{2}=!_{0}$ U. In this regime the ground-state doublet of the isolated molecule

is composed of the states 1/2;0i and 1/2;0i, degenerate at the symmetric point. The low-energy excitations of the full system are now charge uctuations and there is a large gap for spin uctuations. The low-energy excitations are described by an elective K ondo model in which the role of the spin is played by a pseudo-spin variable that represents the two states of the lowest lying doublet. A priori there is no rotational invariance in pseudo-spin space and, in fact, in the elective H am iltonian two di erent matrix elements appear: $h2;0H_{M} \ge j;m$ in ;m $H_{M} \ge 1/2;0i / 1/0 J^{T+}$ jn if, and $h2;0H_{M} \ge j;m$ in ;m $H_{M} \ge 1/2;0i / h0J^{T+}$ jn if , and $h2;0H_{M} \ge j;m$ in ;m $H_{M} \ge 1/2;0i / h0J^{T+}$ jn if thus the anisotropic K ondo model (AKM) with

$$J_{(k;?)} = 0 \qquad \frac{8}{U} \sum_{m=0}^{N^{1}} (1)^{m} \frac{30 y^{r} + jm i j^{2}}{\frac{2}{!} \frac{2}{0} U} + \frac{2m ! 0}{U}; \qquad (9)$$

and K ondo tem perature T_{AKM} given by [17]:

couplings J_k and J_2 given by

$$\Gamma_{AKM} / D J_{?} = J_{k}^{\frac{1}{J_{k} 0}}$$
: (10)

A sym ptotically, $J_{?}=J_{k}$ exp $2\left(=!_{0}\right)^{2}$ and $T_{A\,K\,M}$ exp $\left(=!_{0}\right)^{4}$ with = $!_{0}$ = . In this regime the K ondo tem perature decreases sharply with increasing . In contrast to the weak e-ph coupling case, no C oulom b blockade peaks are expected for $T > T_{A\,K\,M}$. A nother important di erence from the weak case is that, now, the charge susceptibility (/ $T_{A\,K\,M}^{1}$) is very large. Then, the width of the conductance peak versus gate voltage " $_{d}$ $T_{A\,K\,M}$ also decreases sharply as increases. The region in the T $"_{d}$ plane where G G_{0} is thus strongly suppressed by a strong e-ph coupling.

We now turn to the discussion of our numerical results obtained using the NRG method [18, 19]. The original NRG method has been modiled to include e-ph coupling [20] and to calculate the spectral density $_{\rm d}$ (!) according to Ref. [21]. We have performed calculations for a broad range of parameters. We set $k_{\rm B}$ = 1 and take the half-bandwidth of the electrodes as the unit of energy. In the following, we present results for the set of parameters = 0.016, ! $_{0}$ = 0.05 and U = 0.1.

Figure 1 shows the linear conductance G as a function of the gate voltage "d for T = 0 and T = and several values of the e-ph coupling . For = 0 [Fig.1 (a)] and T = the C oulom b blockade peaks [22, 23] separated by the charging energy U are clearly seen. W ith decreasing T the conductance in the C oulom b blockade valley increases as the K ondo e ect develops. At zero tem perature G has a single peak of width "d U centered at " $_{d}^{2}$. The main e ect of a weak coupling to the vibrational m ode at nite T [Fig.1 (b)] is a reduction of the distance between the C oulom b blockade peaks, now given by U_e as anticipated above. The width of the T = 0 peak is also of the order of U_e. This large width is a consequence of

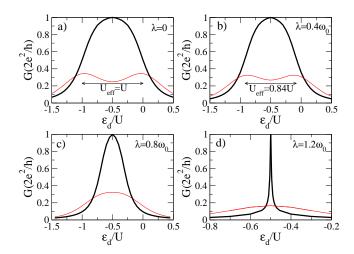


FIG.1: Conductance G versus gate voltage $"_d$ for di erent values of (a-d). (thick lines: T = 0, thin lines: T = 0.016). Param eters are U = 0:1, = 0:016 and ! _0 = 0:05.

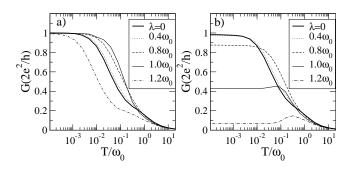


FIG.2: Zero-bias conductance G versus temperature T for di erent values of . (a) Symmetric point " $_{\rm d}$ = U=2 =

0.05. (b) A symmetric case, $"_d = "_d$ $"_d^2 = 0.01$. O ther parameters as in Fig. 1.

the rigidity of the ground state of the molecule against charge uctuations.

For strong e-ph coupling \mathbb{F} ig.1 (d)] the features change qualitatively. A single peak is observed in the conductance at all temperatures and its width sharply decreases with T. The peak narrowing results from the dramatic increase of the charge susceptibility of the molecule in the strong coupling regime. Moving away from the sym – metric point by application of a gate voltage produces an e ect similar to that of applying a magnetic eld in the standard K ondo e ect [24]: the degeneracy of the ground-state doublet is broken and the K ondo resonance in the spectral density is destroyed [25].

 $\begin{array}{rcl} For U_e & . & \ensuremath{\left[Fig.1 (c) \right]} \ensuremath{\text{the system is in a m ixed valence}} \\ regime in which the four charge states of the molecule are nearly degenerate for "_d & $n_d^{$\!\!\!\!}$. A single peak is then observed in the conductance at all tem peratures with a T = 0 width that is determined by the hybridization \\ \end{array}$

In all regimes discussed so far, the T = 0 conductance at $"^{?}_{d}$ is perfect as required by Eq. (6).

Figure 2 shows the T-dependence of G for several val-

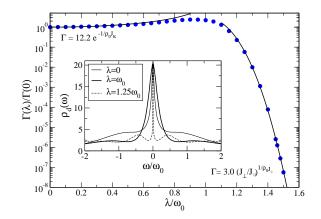


FIG.3: Full width at half maximum of the central peak in the spectral density $_{\rm d}$ versus at the symmetric point " $_{\rm d} = "_{\rm d}^2$. Solid lines are ts based on the given analytical expressions (see text). Inset: $_{\rm d}$ (!) for three values of . O ther parameters as in Fig. 1.

ues of . At the symmetric point $\operatorname{Fig} 2(a)$] G G₀ below a temperature scale that depends on the coupling. This scale varies non-monotonically with , rst increasing and then decreasing. For very small the behavior in the asymmetric case $\operatorname{Fig} 2(b)$] is similar to the previous one. For the larger couplings, however, G G₀ at all temperatures.

The inset in Fig. 3 shows the spectral density $_{\rm d}$ (!) at the symmetric point for three values of the e-ph coupling. The width of the central peak is renormalized by the interaction. It is also non-monotonic as a function of

as shown in the main plot where ts to the theoretical expressions discussed above are also shown. For weak coupling region we use = A exp [$1=(J_k \ _0)$] with J_K given by Eq.(8). For strong coupling we use = A $^0 T_{AKM}$ with T_{AKM} given by Eq.(10), instead. Only the amplitudes A; A⁰ are thing parameters. It can be seen from Fig.3 that the agreement with the predicted widths () is excellent. For intermediate couplings the charge uctuations are no longer blocked by the C oulomb interaction and the system is in the mixed valence regime where = O().

Figure 4 shows the spectral density for strong e-ph coupling and several values of "d 0. At the sym metric point there are peaks at the energies of the isolated molecule given by Eq.(7). There is also a peak at the Ferm i level associated with the charge K ondo effect. Its width is proportional to T_{AKM} [Eq. (10)]. For T_{AKM} there is little change in the spectral deni"ai sity. W hen the asymmetry increases, spectral weight is transferred from positive to negative energies ! and $_{\rm d}$ (0) is suppressed. For j $"_{d}\,j\!>\,T_{A\,K\,M}$, the central peak disappears and alm ost all the spectral weight is concentrated in the negative ! region. The behavior for positive $"_{d}$ is obtained through the transform ation ! ! !. This spectral polarization is the result of the strong charge

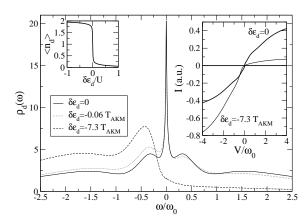


FIG.4: Spectral density $_{\rm d}$ for di erent values of the asymmetry $m_{\rm d} = m_{\rm d} = m_{\rm d}^2$ in the strong e-ph coupling regime (= 12!_0). Here $T_{\rm AKM} = 0.0012$. Left inset: average charge $h_{\rm d}$ i in the molecule as a function of the asymmetry. Right inset: current-voltage curves showing rectication in the asymmetric case. O ther parameters as in Fig. 1.

polarization induced by the asym m etry. It is illustrated in the left inset to F igure 4 that shows the ground-state charge of the m olecule $\rm ln_di$ as a function of "d. It can be seen that charge uctuations in the molecule are rapidly suppressed for j "dj& $T_{\rm AK\,M}$.

An interesting consequence of this spectral asymmetry is that the molecular device exhibits strong rectifying properties in the strong e-ph coupling limit. The right inset to Fig. 4 shows the current-voltage (I V) characteristics for the device in this regime [26]. At the symmetric point, the I V curve is symmetric around zero bias V and it exhibits some structures associated to the peaks in the spectral density. In the asymmetric case (with " $_{\rm d} < 0$), the molecule is polarized and the I V curve is asymmetric: the current for negative bias V is much larger than for positive V (the opposite occurs for " $_{\rm d} > 0$).

In sum m ary, we have studied the transport properties of a m olecular device including e-e and e-ph interactions. We have shown that at low temperatures and weak eph coupling, the conductance properties of the m olecular junction are described by the standard K ondo m odel with renorm alized parameters. At large e-ph coupling, new physics appears: the properties of the device are described in terms of a charge analog of the K ondo e ect. In this regim e the transport properties of the m olecular junction are controlled by the large charge polarizability of the molecule. The latter induces a strong spectral polarization that leads to a rectifying behaviour of the current-voltage characteristics of the molecular junction.

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- [1] D.L.Klein, et al., Nature 389, 699 (1997).
- [2] J.Park, et al., Nature 417, 722 (2002).
- [3] S.Kubatkin, et al., Nature 425, 698 (2003).
- [4] D.Goldhaber-Gordon, et al., Nature 391, 156 (1998).
- [5] W .Liang, et al., Nature 417, 725 (2002).
- [6] L.H.Yu and D.Natelson, Nano Lett. 4 (1), 79 (2004).
- [7] W .Ho, J.Chem .Phys. 117, 11033 (2002).
- [8] H. Park, et al, Nature 407, 57 (2000).
- [9] A. Heeger, S. Kivelson, J. R. Schrie er, and W. P. Su, Rev. M od. Phys. 60, 781 (1988).
- [10] A.M itra, I.A leiner, and A.M illis, cond-m at/0302132.
- [11] K.Flensberg, Phys. Rev. B 68, 205323 (2003).
- [L2] D.M.-T.Kuo and Y.C.Chang, Phys.Rev.B 66, 085311 (2002).
- [13] Y.M eir and N.S.W ingreen, Phys. Rev. Lett. 68, 2512 (1992).
- [14] A.P.Jauho, N.S.W ingreen, and Y.M eir, Phys.Rev.B 50, 5528 (1994).
- [15] A.C. Hewson, The Kondo Problem to Heavy Fermions (Cambridge University Press, 1997).
- [16] For a related calculation see: W . Stephan, M . Capone, M . Grilli, and C . Castellani, Phys. Lett. A 227 (1-2), 120 (1997).
- [17] T.A. Costi and C. Kie er, Phys. Rev. Lett. 76, 1683 (1996); T.A. Costi, Phys. Rev. Lett. 80, 1038 (1998).
- [18] K.G.W ilson, Rev.M od.Phys. 47, 773 (1975).
- [19] H. R. Krishna-murthy, J. W ilkins, and K. G. W ilson, Phys. Rev. B 21, 1003 (1980).
- [20] A.C. Hew son and D.M eyer, J. Phys. Condens. M atter 14, 427 (2002).
- [21] W .Hofstetter, Phys.Rev.Lett.85, 1508 (2000).
- [22] L. I. G lazm an and M. E. Raikh, JETP Lett. 47, 452 (1988).
- [23] T.K.Ng and P.A.Lee, Phys. Rev. Lett. 61, 1768 (1988).
- [24] T.A.Costi, Phys. Rev. B 64, 241310(R) (2001).
- [25] The charge K ondo e ect is robust in the presence of a magnetic eld. N o K ondo peak splitting and no suppression of the conductance is expected to occur upon application of a magnetic eld in the strong e-ph coupling regime.
- [26] Here we simply assume that $_{d}$ (";V) $_{d}$ (";V = 0), assumption valid for small V and calculate the current using I / d" [f (" + eV) f (")] $_{d}$ (").